

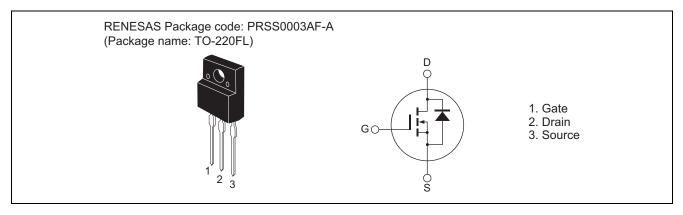
Silicon N Channel MOS FET High Speed Power Switching

#### R07DS0422EJ0100 Rev.1.00 May 26, 2011

## Features

- Low on-resistance
- $R_{DS(on)} = 1.35 \ \Omega \text{ typ.}$  (at  $I_D = 3 \text{ A}$ ,  $V_{GS} = 10 \text{ V}$ ,  $Ta = 25^{\circ}\text{C}$ )
- Low leakage current
- High speed switching

## Outline



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

-			(14 - 25 C)
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	500	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	ID <sup>Note4</sup>	6	А
Drain peak current	Note1 I <sub>D (pulse)</sub>	18	А
Body-drain diode reverse drain current	I <sub>DR</sub>	6	А
Body-drain diode reverse drain peak current	Note1 I <sub>DR (pulse)</sub>	18	А
Avalanche current	I <sub>AP</sub> <sup>Note3</sup>	4	А
Avalanche energy	E <sub>AR</sub> <sup>Note3</sup>	0.88	mJ
Channel dissipation	Pch Note2	28.5	W
Channel to case thermal impedance	θch-c	4.38	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1.  $PW \leq 10~\mu s,~duty~cycle \leq 1\%$ 

2. Value at Tc = 25°C

- 3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area



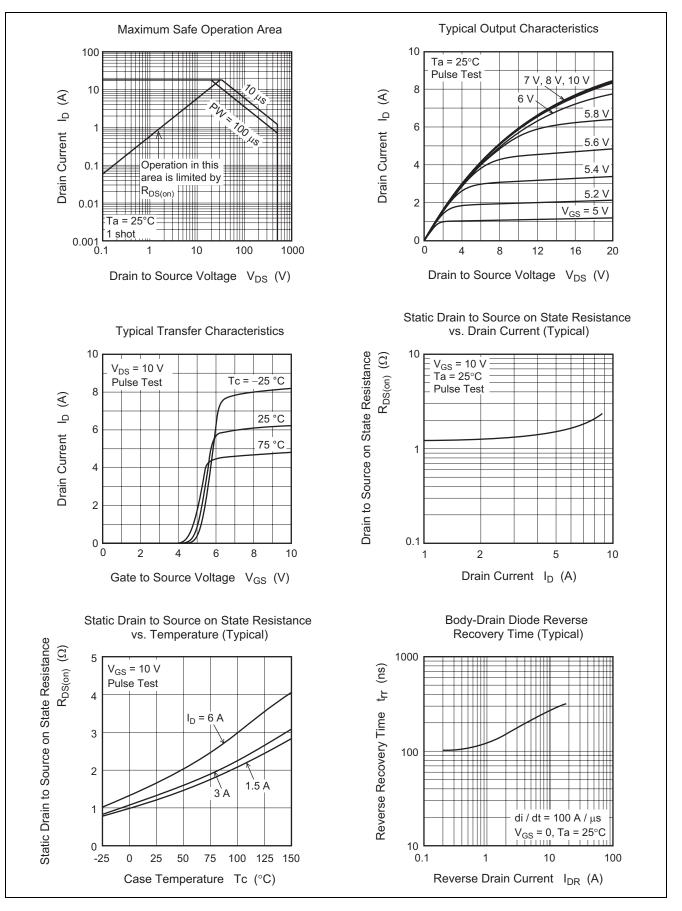
# **Electrical Characteristics**

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	500			V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>			1	μΑ	$V_{DS} = 500 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	_	1.35	1.70	Ω	$I_D = 3 \text{ A}, V_{GS} = 10 \text{ V}^{Note5}$
resistance						
Input capacitance	Ciss		440		pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss		52	—	pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss		7	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	26	_	ns	I <sub>D</sub> = 3 A
Rise time	tr	_	19		ns	$V_{GS} = 10 V$ $R_L = 83.3 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	t <sub>d(off)</sub>	_	50		ns	
Fall time	t <sub>f</sub>	_	14		ns	
Total gate charge	Qg	_	14		nC	V <sub>DD</sub> = 400 V
Gate to source charge	Qgs	_	2.5		nC	V <sub>GS</sub> = 10 V I <sub>D</sub> = 6 A
Gate to drain charge	Qgd	_	6.9		nC	
Body-drain diode forward voltage	V <sub>DF</sub>		0.95	1.50	V	$I_F = 6 A, V_{GS} = 0^{Note5}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	230		ns	$I_F = 6 A, V_{GS} = 0$
						di <sub>F</sub> /dt = 100 A/µs

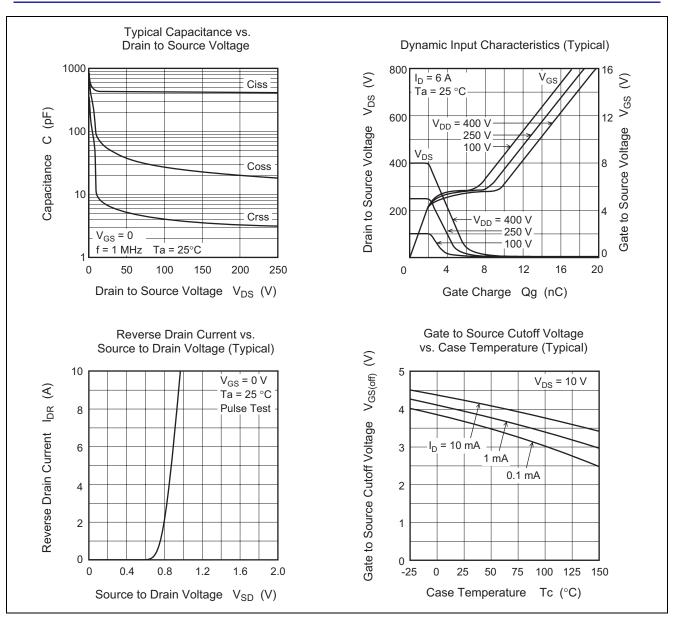
Notes: 5. Pulse test



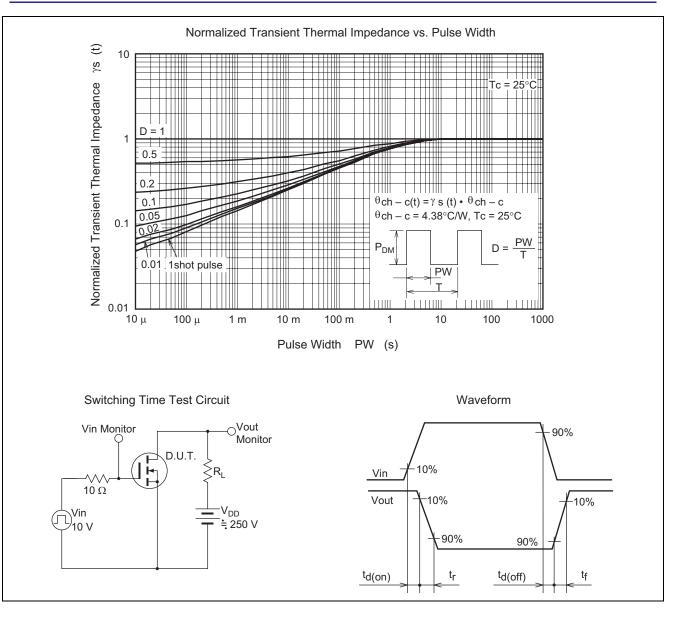
### **Main Characteristics**





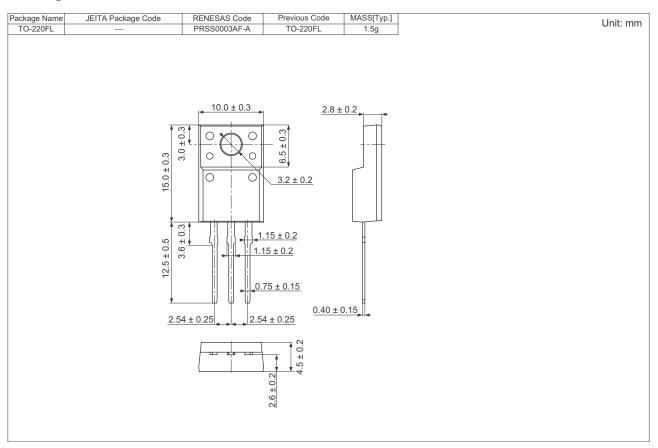








### **Package Dimensions**



## **Ordering Information**

Orderable Part Number	Quantity	Shipping Container
RJK5026DPP-M0-T2	600 pcs	Box (Tube)



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